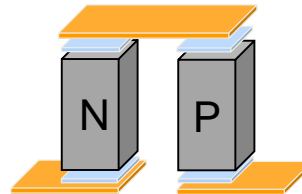


*UK Thermoelectric Network Meeting
Herriot Watt University, Edinburgh
13th February 2018*

Key Issues in Design and Fabrication of Thermoelectric Modules

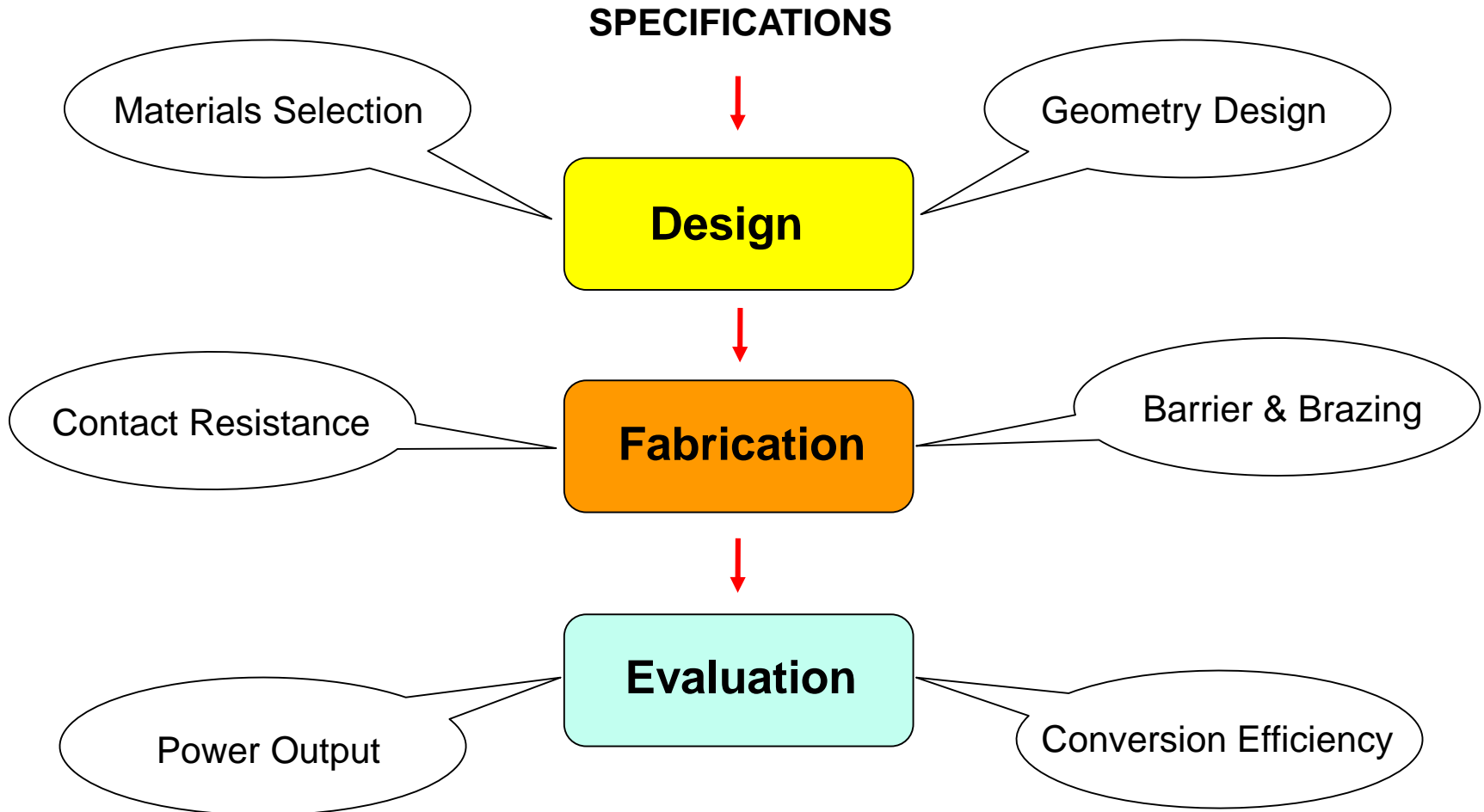


Gao Min

School of Engineering, Cardiff University

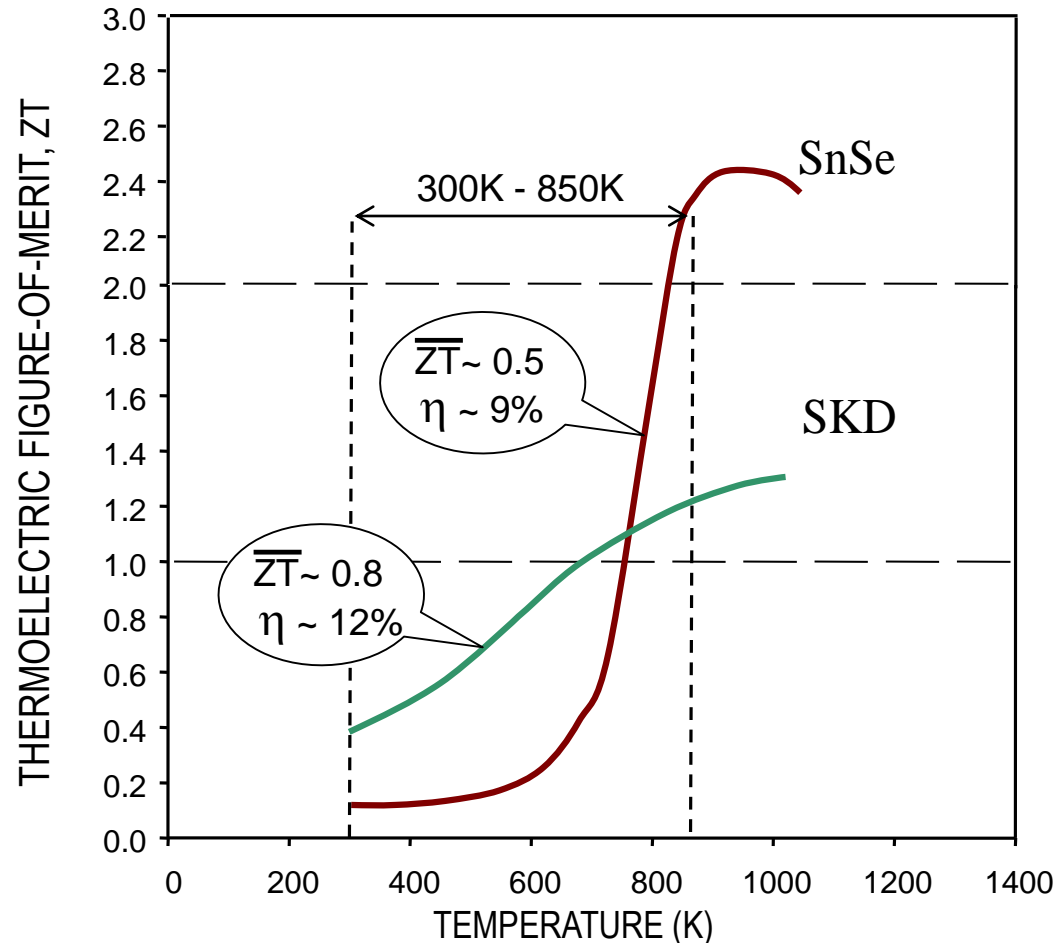


Design and Fabrication Processes



Selection of Thermoelectric Materials

- Large average ZT
- Matching N and P
(e.g. SKD vs Silicide)
- Manufacturability
(e.g. Half-heusler vs SKD)
- Thermal stability
(e.g. Half-heusler vs SKD)
- Non-toxicity
(e.g. Silicide vs PbTe)
- Abundances
(e.g. Silicide vs Bi_2Te_3)



Design of Thermoelement Geometry

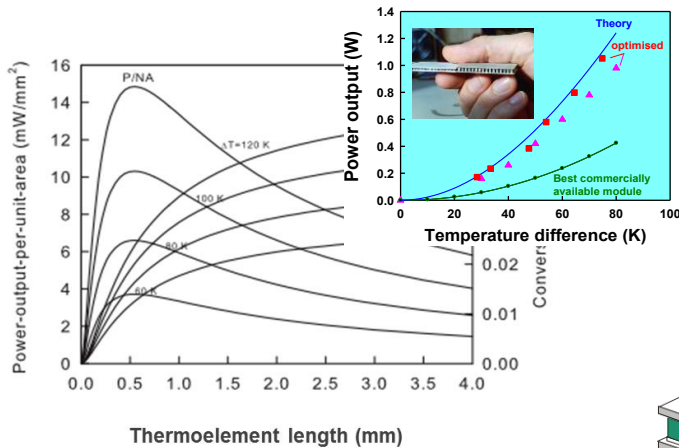
Constant ΔT

Nature of Heat Source

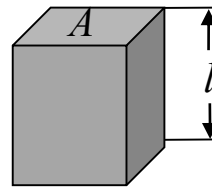
Constant heat flux

$$P_{\max} = \frac{(a \cdot DT)^2}{4r} \frac{A \cdot 2N}{(n+l)(1+2rl_c/l)^2}$$

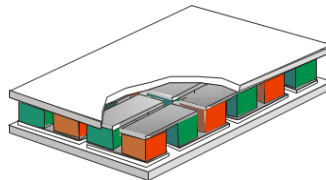
$$f = \frac{\left(\frac{DT}{T_H}\right)}{\left(1+2r\frac{l_c}{l}\right)^2 \left(2 - \frac{1}{2} \frac{DT}{T_H} + \frac{4}{ZT_H} \frac{l+n}{l+2rl_c}\right)}$$



Shorter legs (down to ~500 μ m)

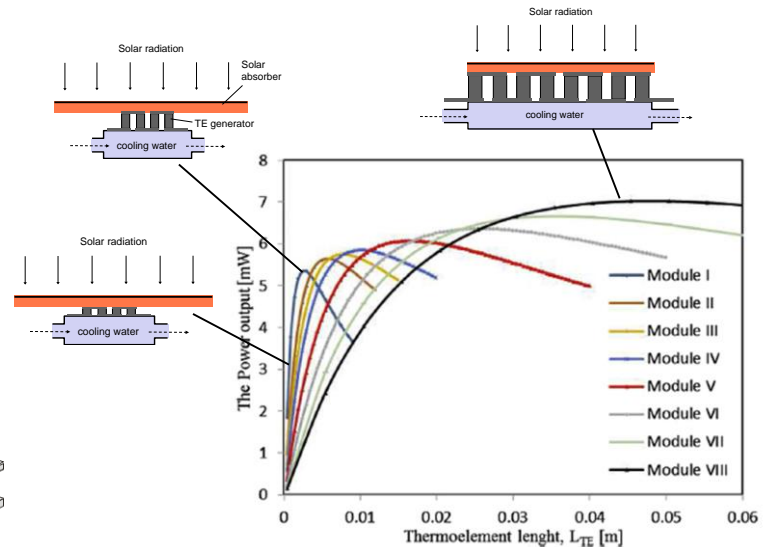


$A/l = ?$



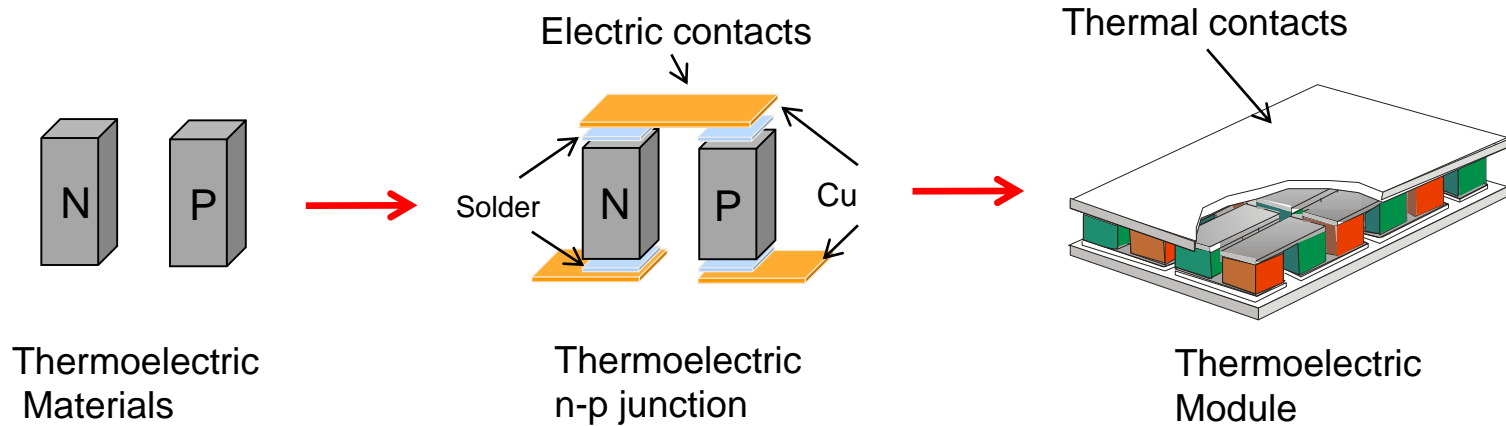
$$P = \frac{s}{(1+s)^2} \times \frac{Z}{(1+ZT_M)^2} \times \frac{\dot{Q}^2}{l} \times \frac{l}{A} \times \frac{l}{(n+l)(1+2rl_c/l)^2}$$

$$f = \frac{P}{\dot{Q}} = \frac{s}{(1+s)^2} \times \frac{Z}{(1+ZT_M)^2} \times \frac{\dot{Q}}{l} \times \frac{l}{A} \times \frac{l}{(n+l)(1+2rl_c/l)^2}$$



Longer legs (typically 3-8 mm)

Materials to Module – Interfaces Challenge

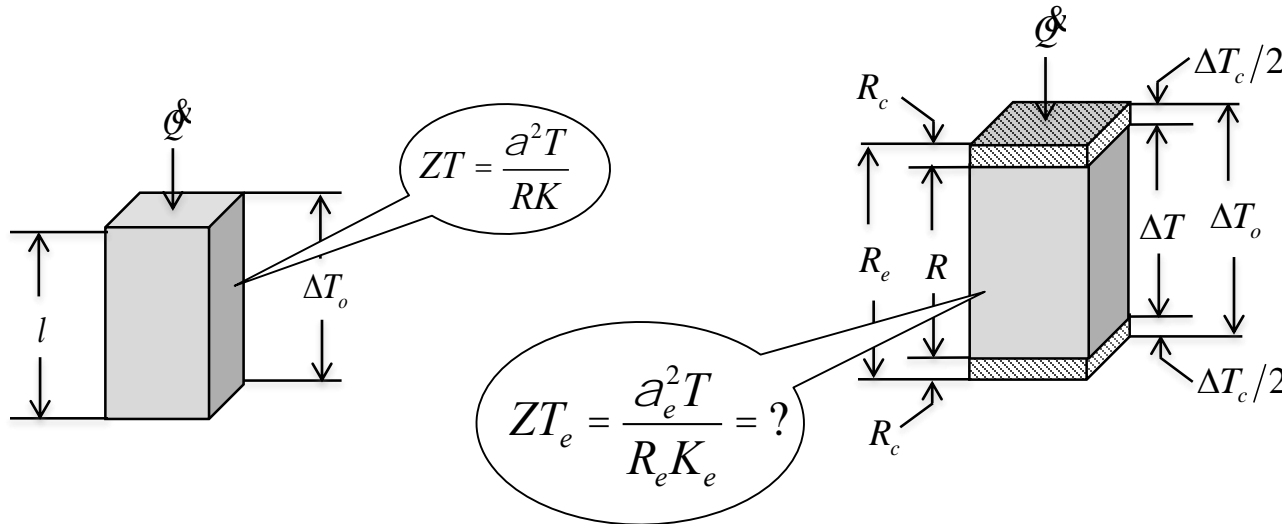


Role: To join and hold the N- and P-type thermoelements together.

Requirements:

- Mechanical strength.
- Temperature stability and durability.
- No reduction in thermoelectric properties.

Influence of Contacts – Theoretical Consideration



Bulk properties:

$$R = \rho(l/A)$$

$$K = \lambda(A/l)$$

Contact properties:

$$R_c = \rho_c/A$$

$$K_c = \lambda_c A$$

$$\frac{ZT_e}{ZT} = \frac{1}{(1 + 2\rho_c/\rho l)(1 + 2\lambda/\lambda_c l)}$$

$ZT_e < ZT$ due to ρ_c, λ_c

$$\alpha_e = \frac{\alpha}{1 + 2\lambda/\lambda_c l}$$

$$R_e = R(1 + \frac{2\rho_c}{\rho l})$$

$$K_e = \frac{K}{1 + 2\lambda/\lambda_c l}$$

ZT will be reduced due to the interfaces. The degree of reduction depends on contact properties, materials properties, and leg length

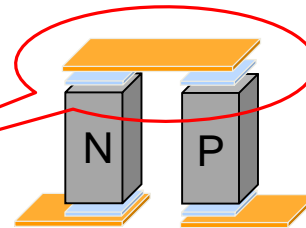
Manufacturing Requirements

Case study based on Bi_2Te_3 : aims to limiting ZT reduction within 10%.

l (mm)	ρ_c (Ωcm^2)	k_c ($\text{W}/\text{m}^2\text{K}$)
0.1	2.6×10^{-7}	5.7×10^5
0.5	1.3×10^{-6}	1.1×10^5
1.0	2.6×10^{-6}	5.7×10^4
1.5	4.0×10^{-6}	3.8×10^4
2.0	5.3×10^{-6}	2.9×10^4
2.5	6.6×10^{-6}	2.3×10^4
3	7.9×10^{-6}	1.9×10^4
5	1.3×10^{-5}	1.1×10^4

Assume:

- 5% due to ρ_c .
- 5% due to λ_c .
- $\rho = 10^3 \Omega\text{cm}$.
- $\lambda = 1.5 \text{ W}/\text{mK}$.



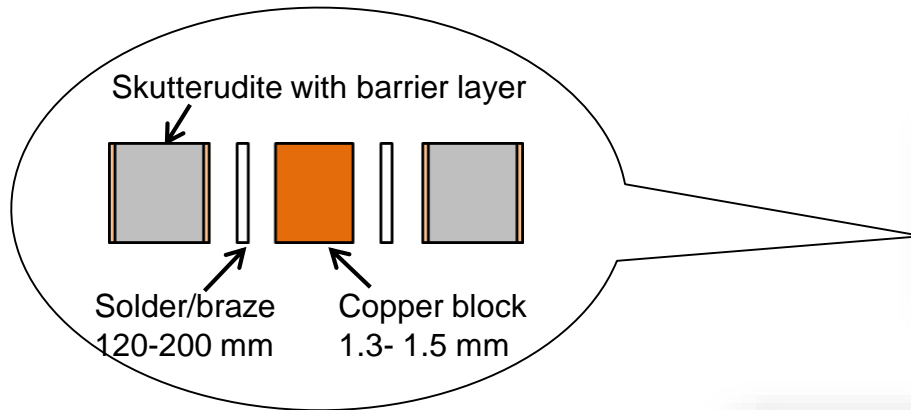
$$\frac{ZT_e}{ZT} = \frac{1}{(1+2\rho_c/\rho l)(1+2\lambda/\lambda_c l)} = 90\%$$

L = 2mm

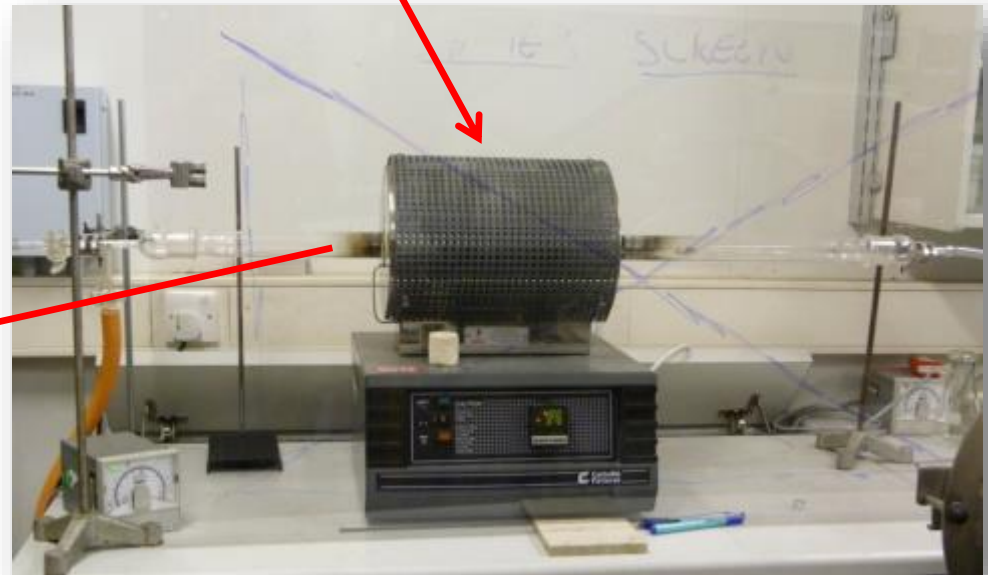
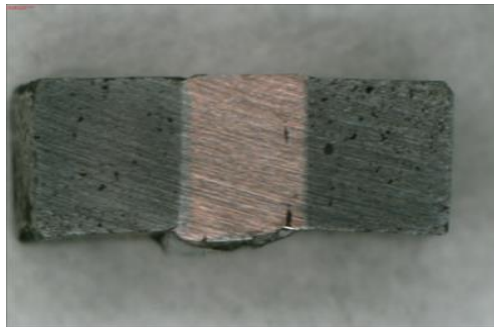
It requires:

$\rho_c \sim 5 \times 10^{-6} \Omega\text{cm}^2$ and $\lambda_c \sim 3 \times 10^4 \text{ W}/\text{m}^2\text{K}$

Sample Preparation for Interface Studies

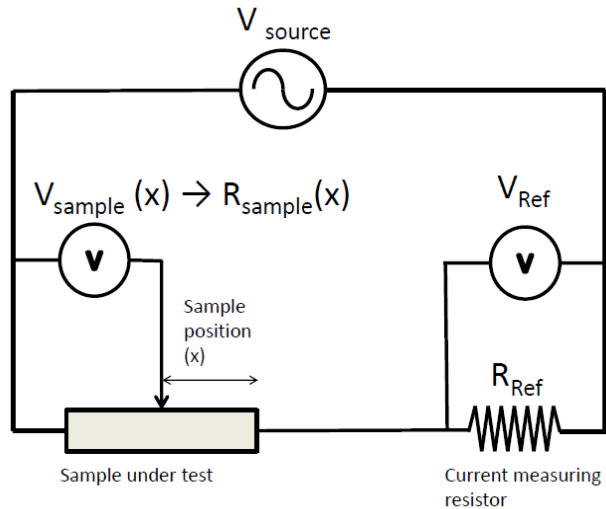


Brazing holder



Brazing (or soldering) in argon gas or vacuum

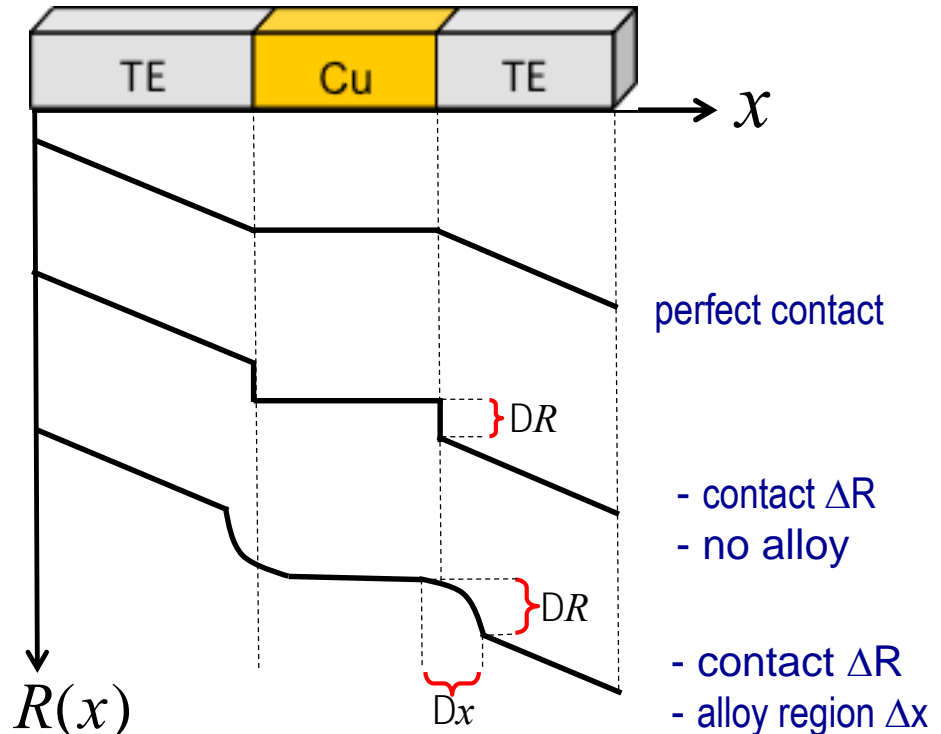
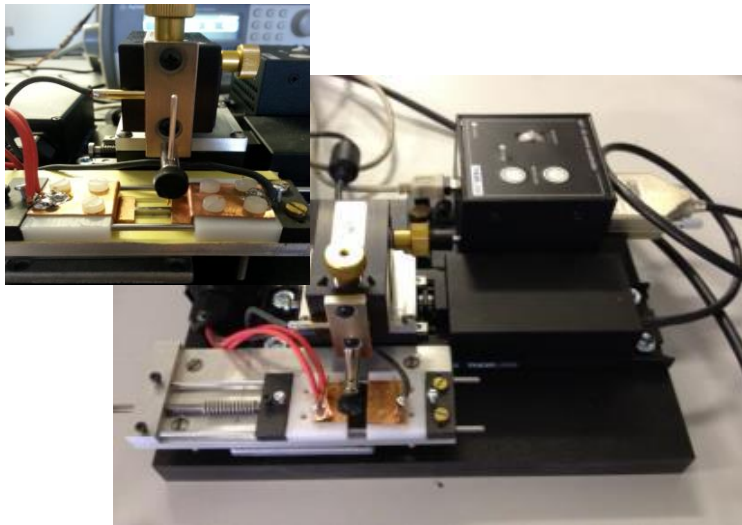
High-resolution Scanning Voltage Probe for Measuring Electrical Contact Resistance



$$R(x) = \frac{V_s(x)}{V_{\text{ref}}} \times R_{\text{ref}}$$

$$r_c = DR \cdot A$$

$$r = dR(x) / dx$$



High Resolution Scanning Voltage Probe (1 μm)

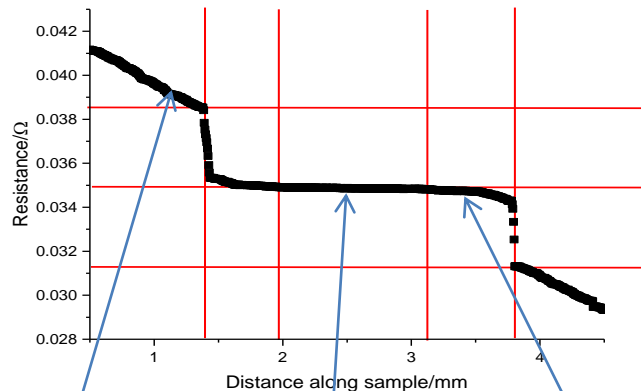
The key is appropriate spatial resolution ($\sim 1\mu\text{m}$ for bulk modules)

Characterisation of Skutterudite Interfaces

SVP Measurement



Pd/Cu/Ag₅₀Cu₂₀Zn₂₈Ni₂



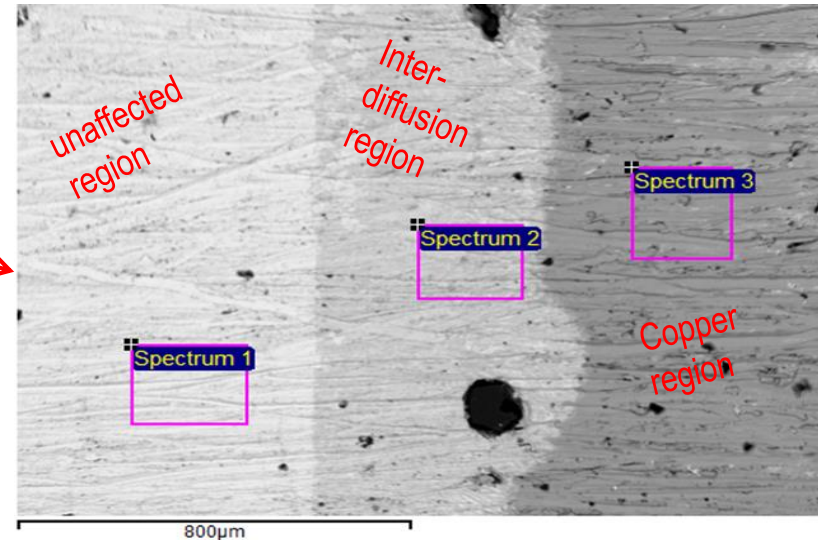
Unaffected region

Copper region

Inter-diffusion region

High resolution scanning voltage probe measurement indicates the formation of alloying region.

SEM and EDX Analysis



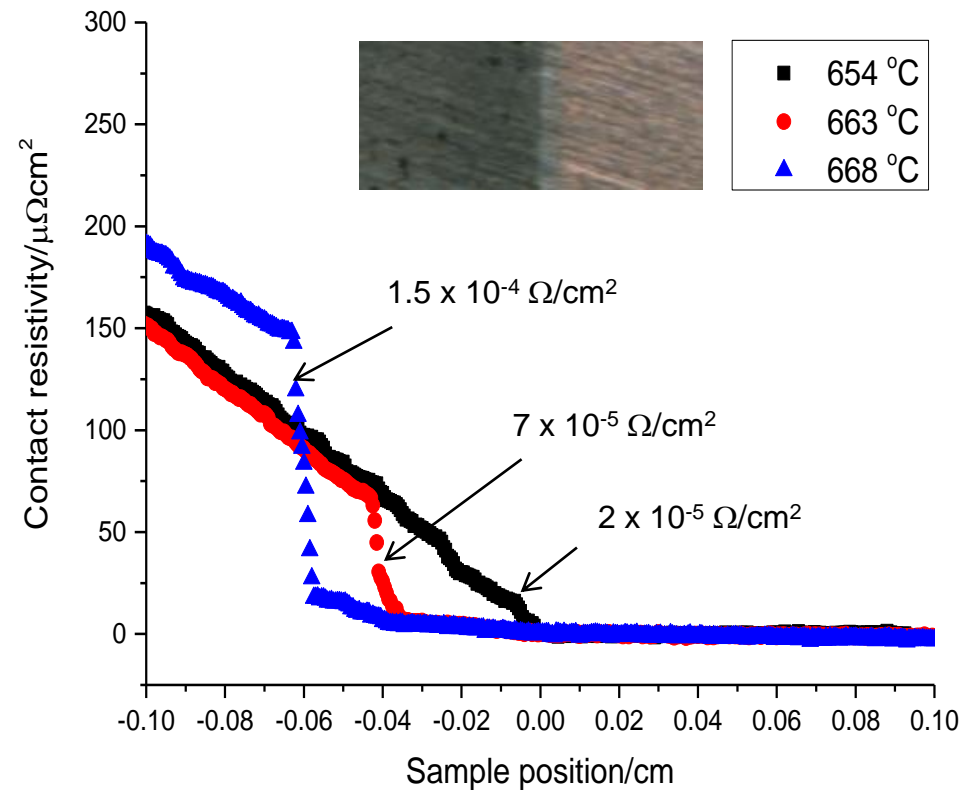
Spectrum	Co	Cu	Zn	Ag	Sb	Total
Spectrum 1	12.29	2.39	0.00	1.93	83.39	100.00
Spectrum 2	3.64	34.17	7.50	14.78	39.90	100.00
Spectrum 3	0.00	97.59	0.00	0.00	2.41	100.00

EDX analysis confirms the formation of the alloying region, which needs to be minimised in good TE modules.

Influence of Brazing Temperature on Interface Quality

INFLUENTIAL FACTORS

- Brazing temperature
- Brazing atmosphere
- Brazing materials
- Thermoelectric materials
- Barrier layers



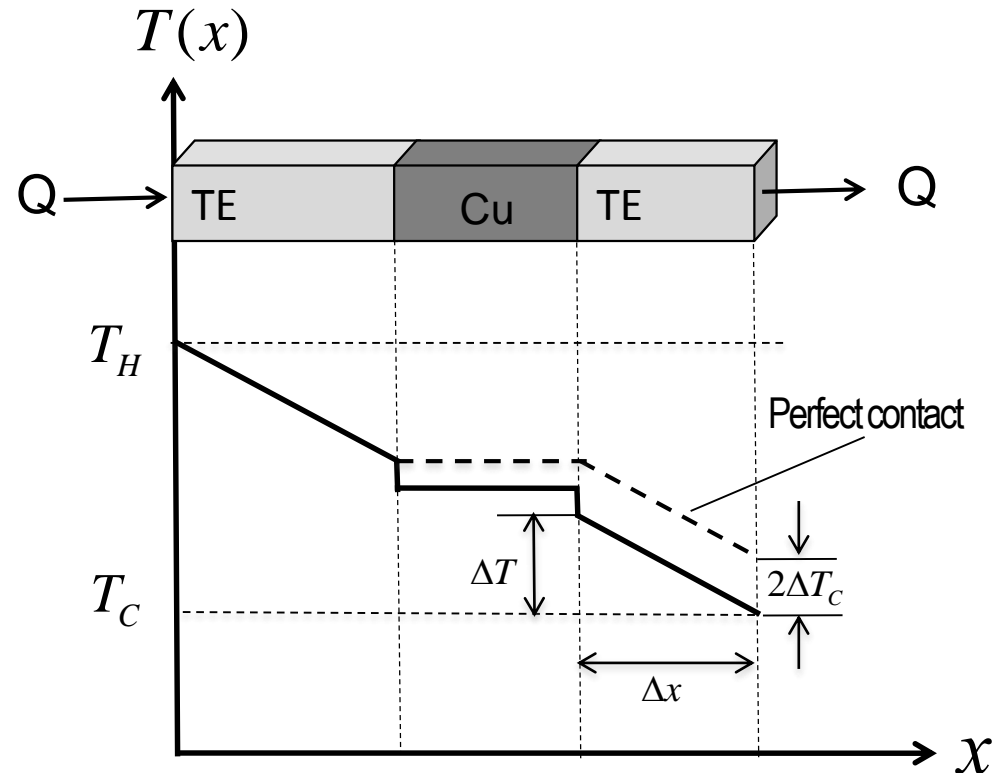
Thermal Contact – Principle of Measurement

Ensure constant heat flow through the sample:

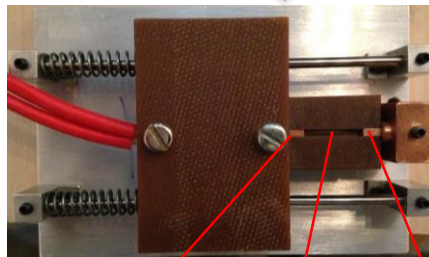
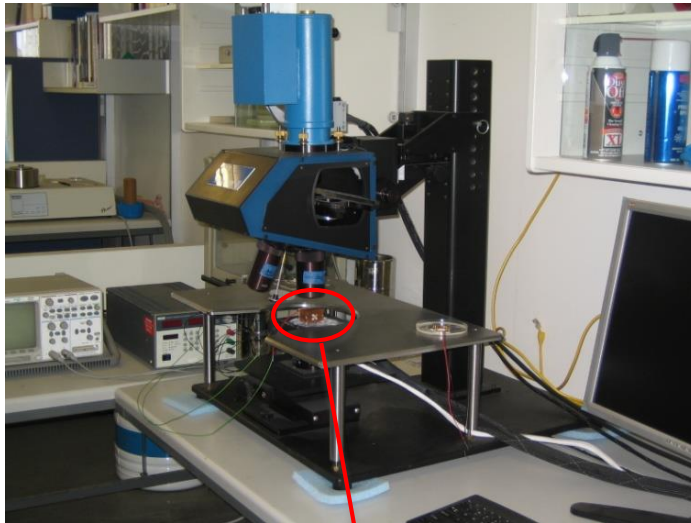
$$\kappa \cdot A \frac{\Delta T}{\Delta x} = \kappa_c \cdot A \cdot \Delta T_c$$

Given k of TE materials and determine ΔT , Δx , and ΔT_c :

$$\kappa_c = \frac{k}{\Delta T_c} \cdot \frac{\Delta T}{\Delta x}$$



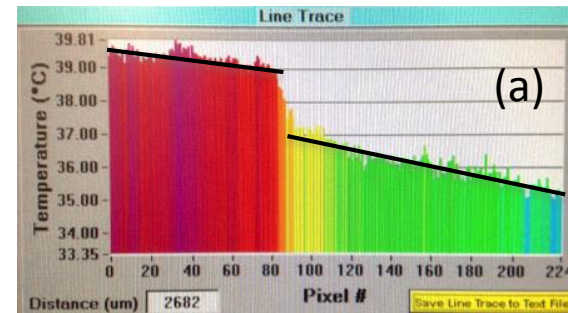
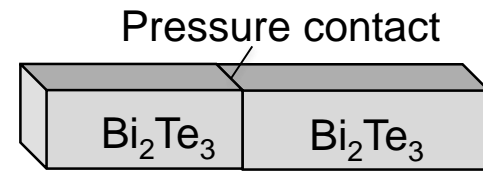
Evaluation of Thermal Contact using IR Microscopy



Hot contact

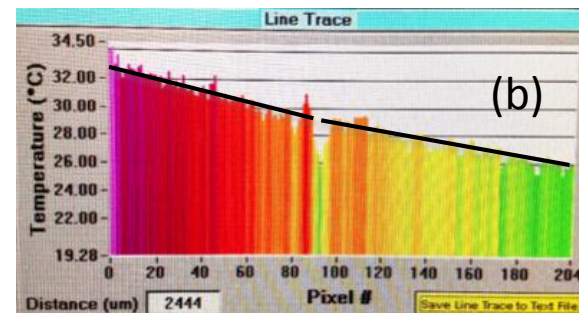
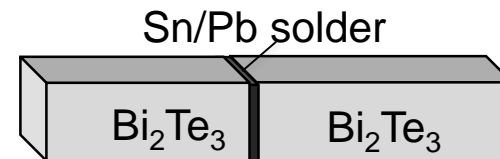
Cold contact

Sample



$$2.4 \times 10^3$$

$$(\text{W}/\text{m}^2\text{K})$$

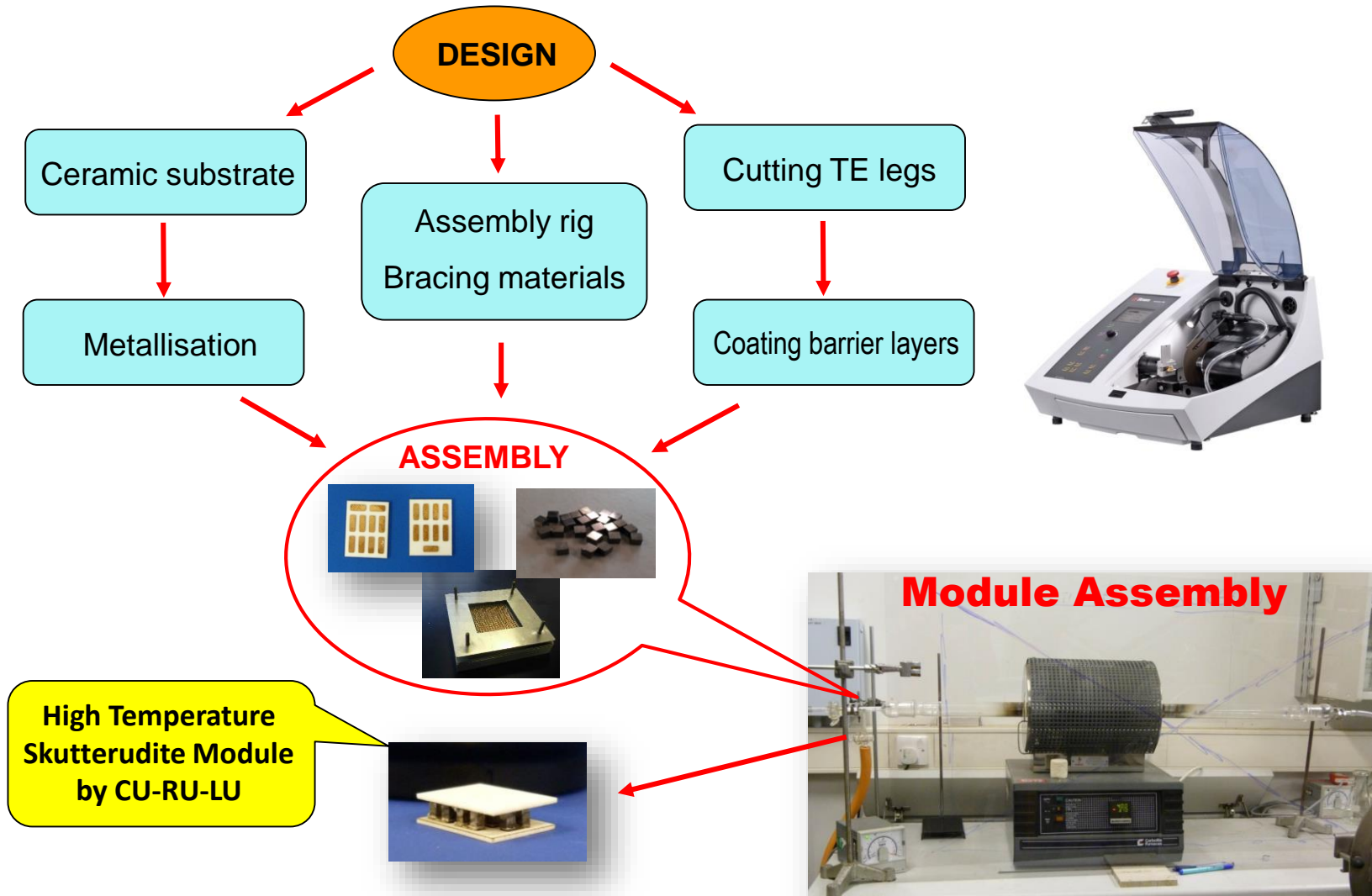


$$4.2 \times 10^4$$

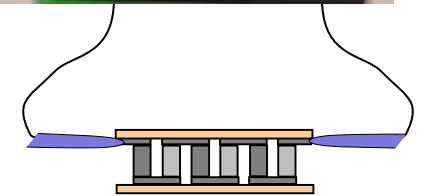
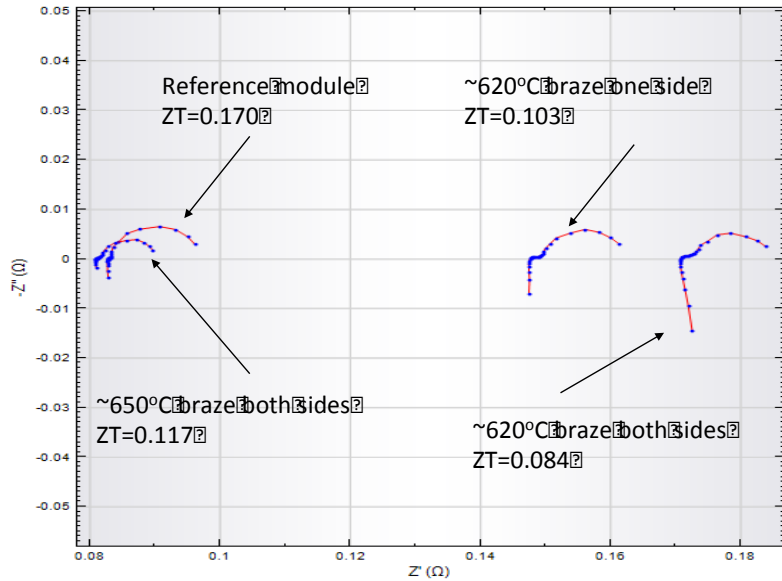
$$(\text{W}/\text{m}^2\text{K})$$

Similar results obtained using indium or heat sink compound

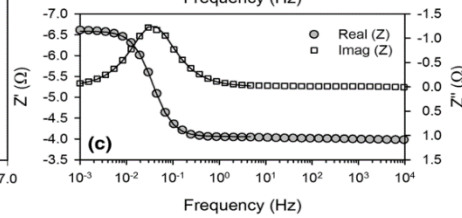
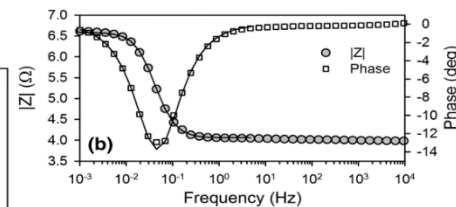
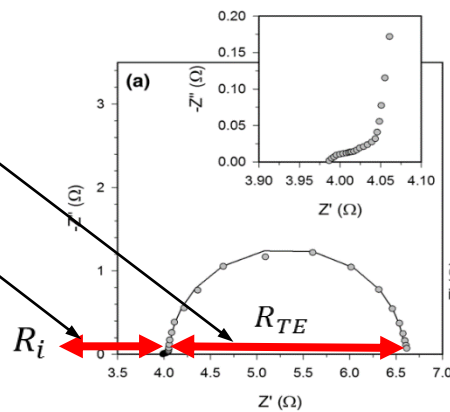
Thermoelectric Module Assembly Process



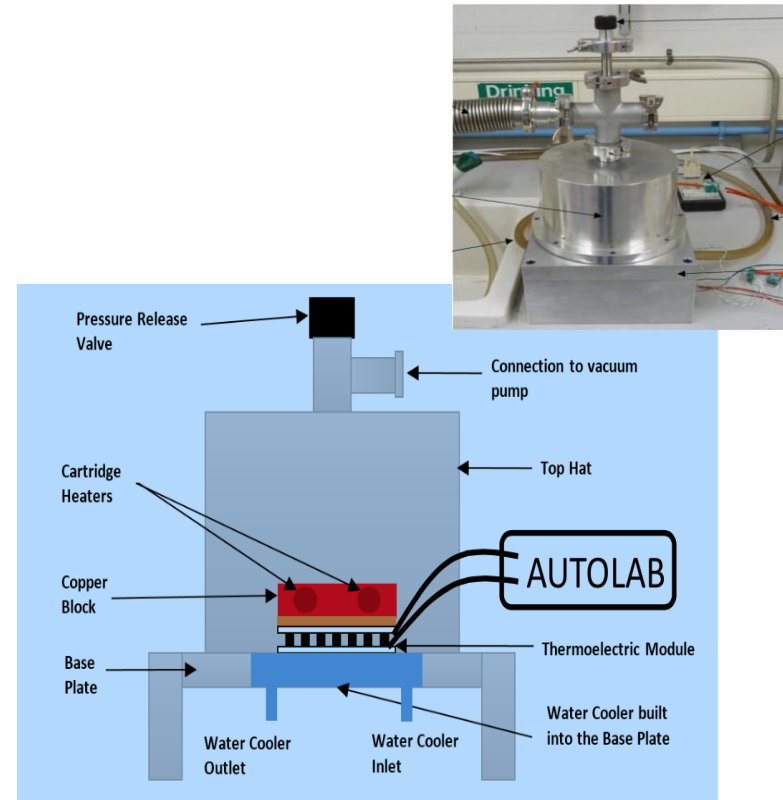
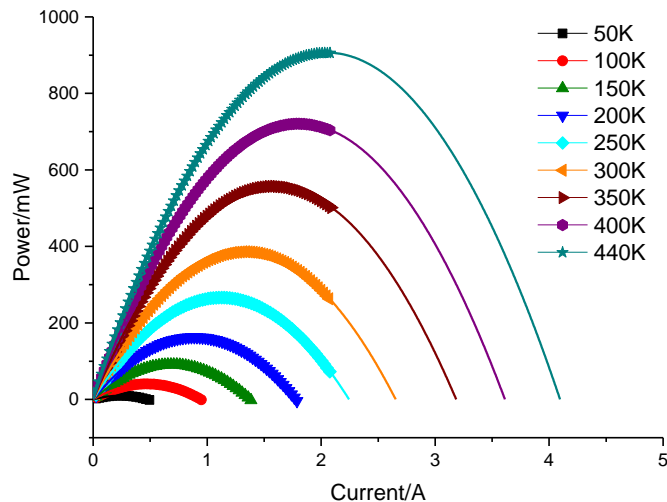
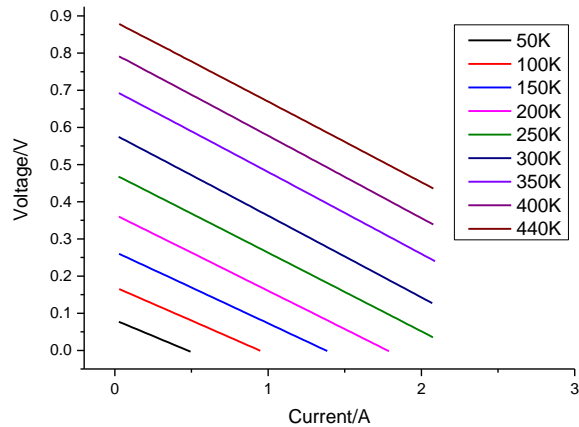
Rapid Screening by Thermoelectric Impedance Spectroscopy



$$ZT = \frac{R_{TE}}{R_i}$$



Determination of Power Output by I-V Curves

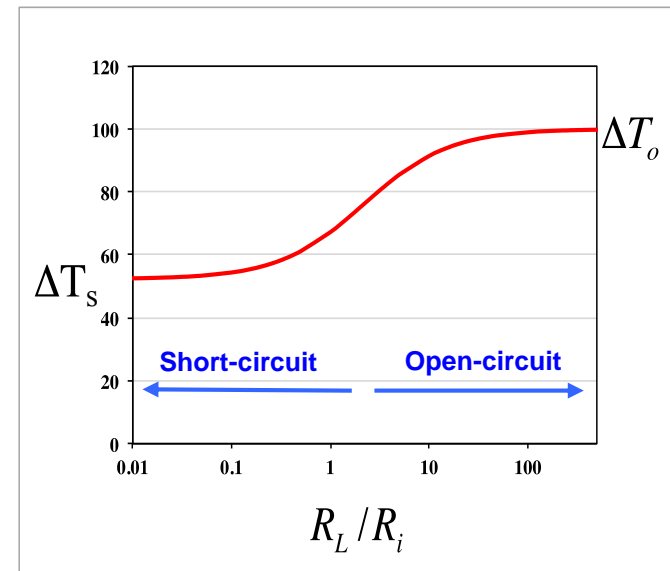
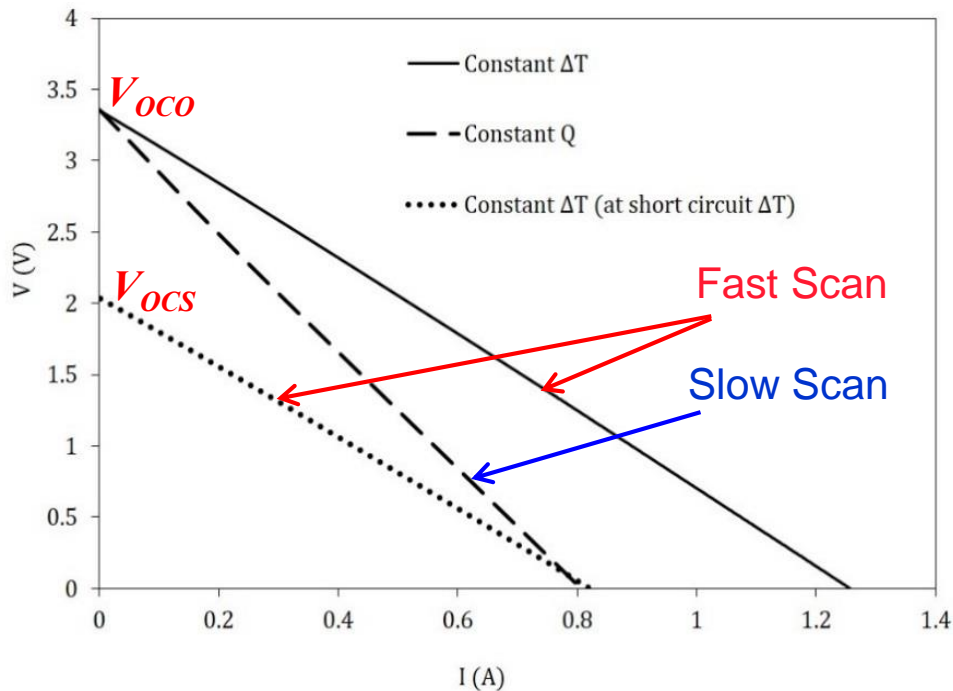


Be aware of errors when used for determining conversion efficiency

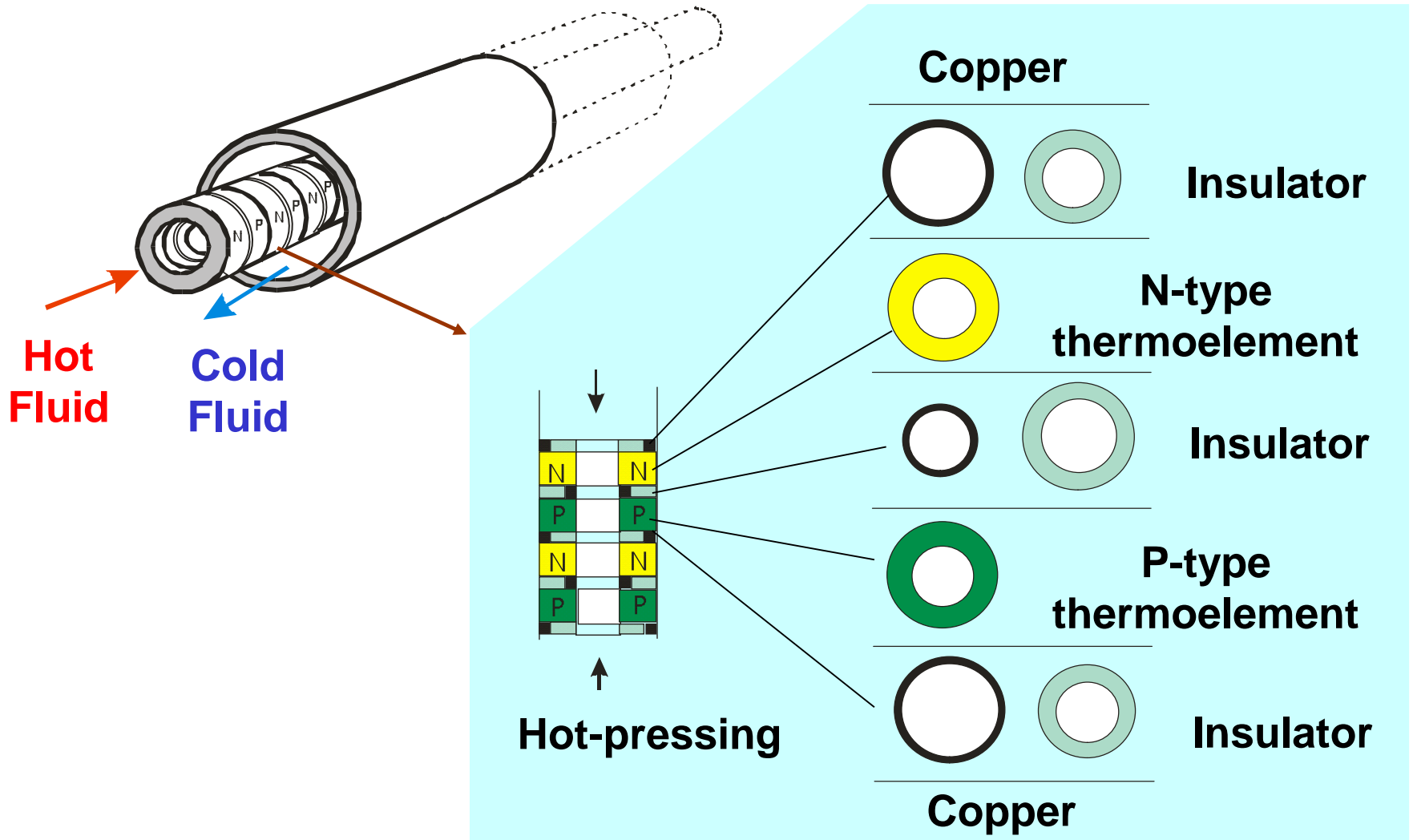
Determine Conversion Efficiency by Triple I-V Curves

$$h_{\max} = \frac{1}{4} \cdot \frac{DT_o}{\bar{T}} \cdot \left(1 - \frac{V_{OCO}}{V_{OCS}} \right)$$

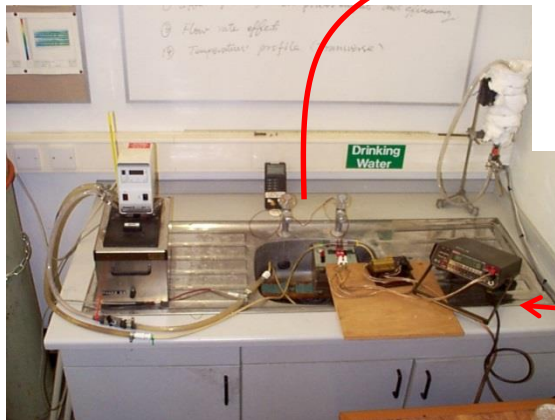
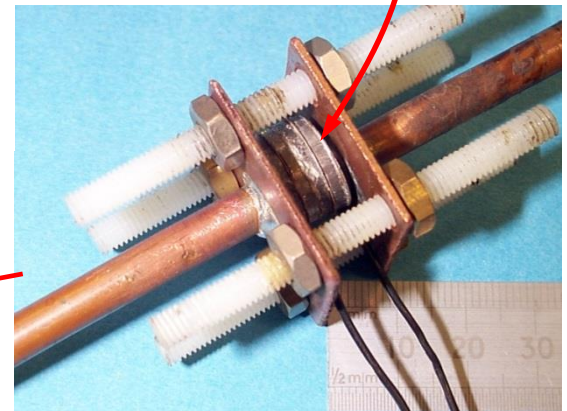
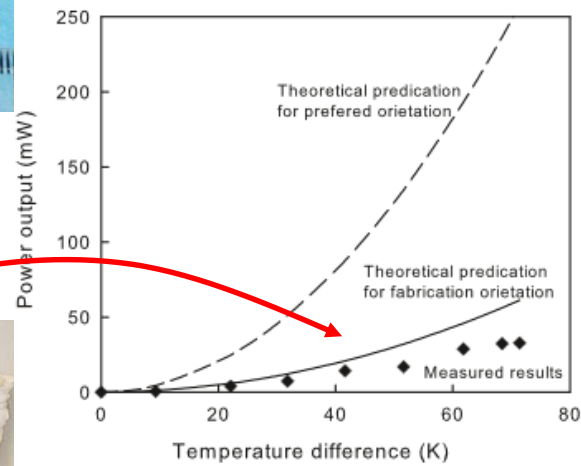
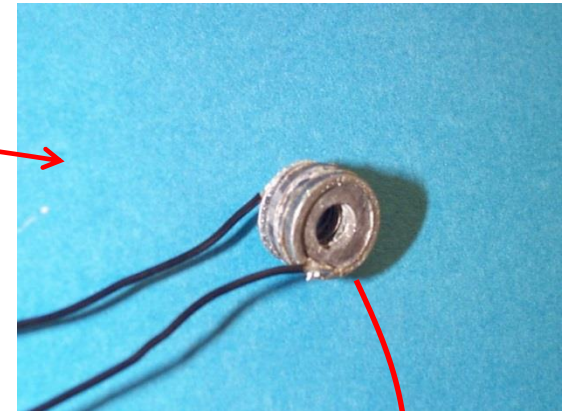
V_{OCO} - corresponding to the first fast scan
 V_{OCS} - corresponding to the second fast scan
Fast Scan – constant temperature difference
Slow Scan – constant heat flux



Ring-structured Thermoelectric Module

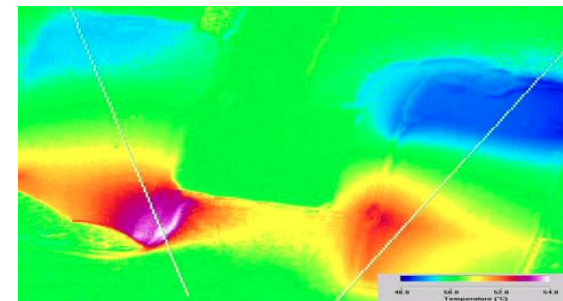
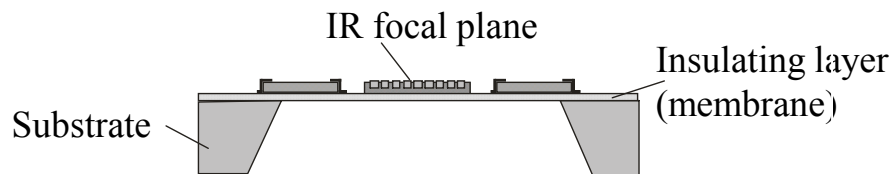
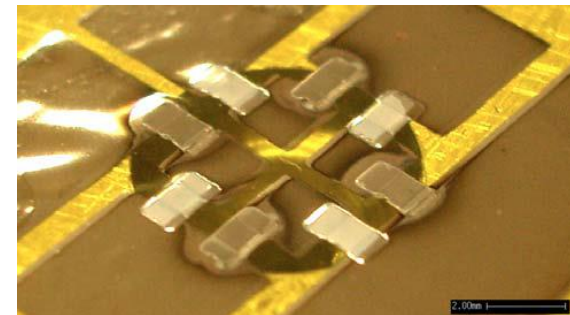
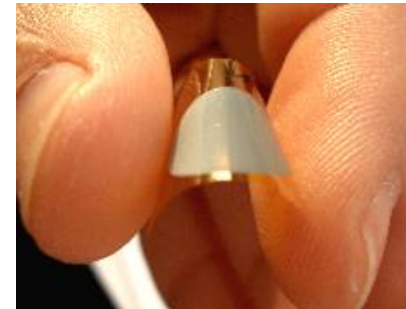
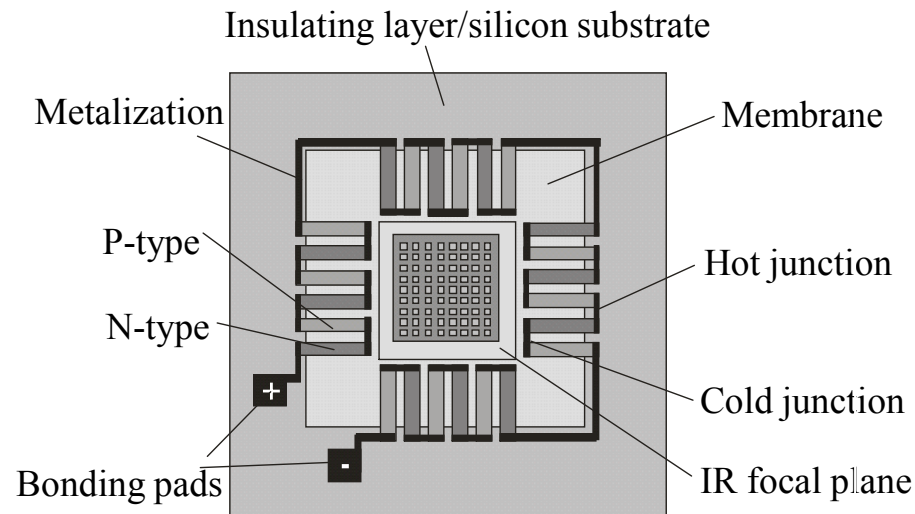


Ring-Structured Thermoelectric Tube



Micro/Nano Converters for Integrated Circuits

Horizontal structure



Ref: G Min and D Rowe, Electronics Letter, 1998, 34(2), 222-223

L.M. Goncalves, P. Alpuim, G. Min, D. M. Rowe, C. Couto, and J. H. Correia, "Optimization of Bi₂Te₃ and Sb₂Te₃ thin films deposited by co-evaporation on polyimide for thermoelectric applications", Vacuum, 82 (12), (2008), 1499-1502

Thank You

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